MOSFET – N-Channel, POWERTRENCH®

80 V, 50 A, 13.4 mΩ

FDMS86380-F085

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
80 V	13.4 mΩ @ 10 V	50 A

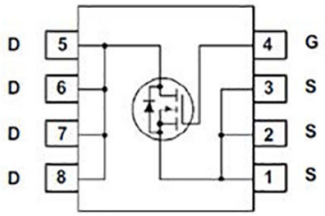
Features

- Typ $R_{DS(on)}$ = 11.3 mΩ at V_{GS} = 10 V; I_D = 50 A
- Typ $Q_{g(tot)}$ = 20 nC at V_{GS} = 10 V; I_D = 50 A
- UIS Capability
- AEC−Q101 Qualified and PPAP Capable
- This Device is Pb−Free, Halogen Free/BFR Free and is RoHS Compliant

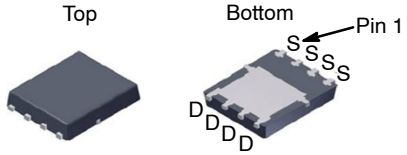
Applications

- Automotive Engine Control
- PowerTrain Management
- Solenoid and Motor Drivers
- Electronic Steering
- Integrated Starter/Alternator
- Distributed Power Architectures and VRM
- Primary Switch for 12 V Systems

ELECTRICAL CONNECTION



N−Channel MOSFET



PQFN8
CASE 483BJ

MARKING DIAGRAM

A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
FDMS86380 = Specific Device Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain−to−Source Voltage		V_{DSS}	80	V
Gate−to−Source Voltage		V_{GS}	±20	V
Continuous Drain Current (V_{GS} = 10 V) (Note 1)	T_C = 25°C	I_D	50	A
Pulsed Drain Current	T_C = 25°C		See Figure 4	
Single Pulse Avalanche Energy (Note 2)		E_{AS}	16	mJ
Power Dissipation		P_D	75	W
Derate above 25°C			0.5	W/°C
Operating and Storage Temperature		T_J, T_{STG}	−55 to +175	°C
Thermal Resistance (Junction−to−Case)		$R_{\theta JC}$	2	°C/W
Maximum Thermal Resistance (Junction−to−Ambient) (Note 3)		$R_{\theta JA}$	50	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Current is limited by bondwire configuration.
2. Starting Tj = 25°C, L = 20 μH, I_{AS} = 40 A, V_{DD} = 80 V during inductor charging and V_{DD} = 0 V during time in avalanche.
3. $R_{\theta JA}$ is the sum of the junction−to−case and case−to−ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design. The maximum rating presented here is based on mounting on a 1 in^2 pad of 2 oz copper.

ORDERING INFORMATION

Device	Package	Shipping†
FDMS86380−F085	PQFN8 (Power 56) (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
B_{VDSS}	Drain−to−Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V		80	–	–	V
I_{DSS}	Drain−to−Source Leakage Current	V_{DS} = 80 V, V_{GS} = 0 V	T_J = 25°C	–	–	1	μA
			T_J = 175°C (Note 4)	–	–	1	mA
I_{GSS}	Gate−to−Source Leakage Current	V_{GS} = ±20 V		–	–	±100	nA
ON CHARACTERISTICS							
$V_{GS(th)}$	Gate−to−Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA		2.0	3.0	4.0	V
$R_{DS(on)}$	Drain−to−Source On−Resistance	I_D = 50 A, V_{GS} = 10 V	T_J = 25°C	–	11.3	13.4	mΩ
			T_J = 175°C (Note 4)	–	25.3	30.0	
DYNAMIC CHARACTERISTICS							
C_{iss}	Input Capacitance	V_{DS} = 40 V, V_{GS} = 0 V, f = 1 MHz		–	1440	–	pF
C_{oss}	Output Capacitance			–	300	–	
C_{rss}	Reverse Transfer Capacitance			–	14	–	
R_g	Gate Resistance	f = 1 MHz		–	2.0	–	Ω
$Q_{g(tot)}$	Total Gate Charge	V_{GS} = 0 to 10 V	V_{DD} = 64 V, I_D = 50 A	–	20	30	nC
$Q_{g(th)}$	Threshold Gate Charge	V_{GS} = 0 to 2 V		–	2.7	–	
Q_{gs}	Gate−to−Source Gate Charge			–	8.8	–	
Q_{gd}	Gate−to−Drain “Miller” Charge			–	4.4	–	
SWITCHING CHARACTERISTICS							
t_{on}	Turn−On Time	V_{DD} = 40 V, I_D = 50 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		–	–	31	ns
$t_{d(on)}$	Turn−On Delay			–	13	–	
t_r	Rise Time			–	8	–	
$t_{d(off)}$	Turn−Off Delay			–	15	–	
t_f	Fall Time			–	5	–	
t_{off}	Turn−Off Time			–	–	30	
DRAIN−SOURCE DIODE CHARACTERISTICS							
V_{SD}	Source−to−Drain Diode Voltage	I_{SD} = 50 A, V_{GS} = 0 V		–	–	1.25	V
		I_{SD} = 25 A, V_{GS} = 0 V		–	–	1.2	
t_{rr}	Reverse Recovery Time	I_F = 50 A, dI_{SD}/dt = 100 A/μs, V_{DD} = 64 V		–	37	55	ns
Q_{rr}	Reverse Recovery Charge			–	23	35	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. The maximum value is specified by design at T_J = 175°C. Product is not tested to this condition in production

TYPICAL CHARACTERISTICS

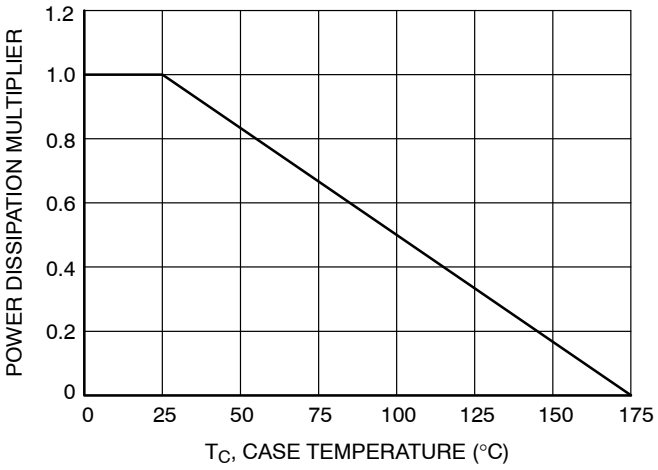


Figure 1. Normalized Power Dissipation vs. Case Temperature

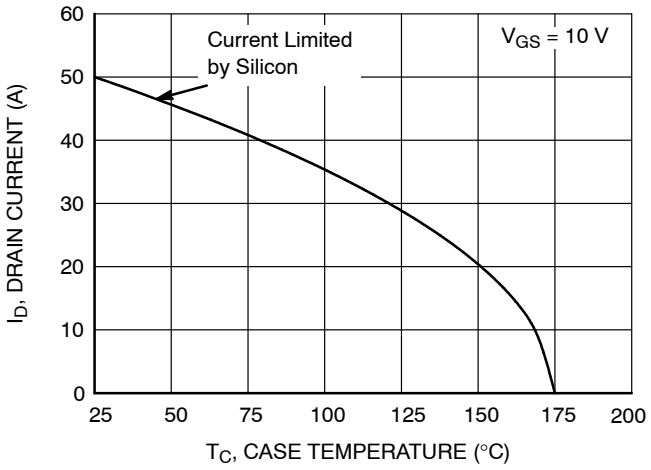


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

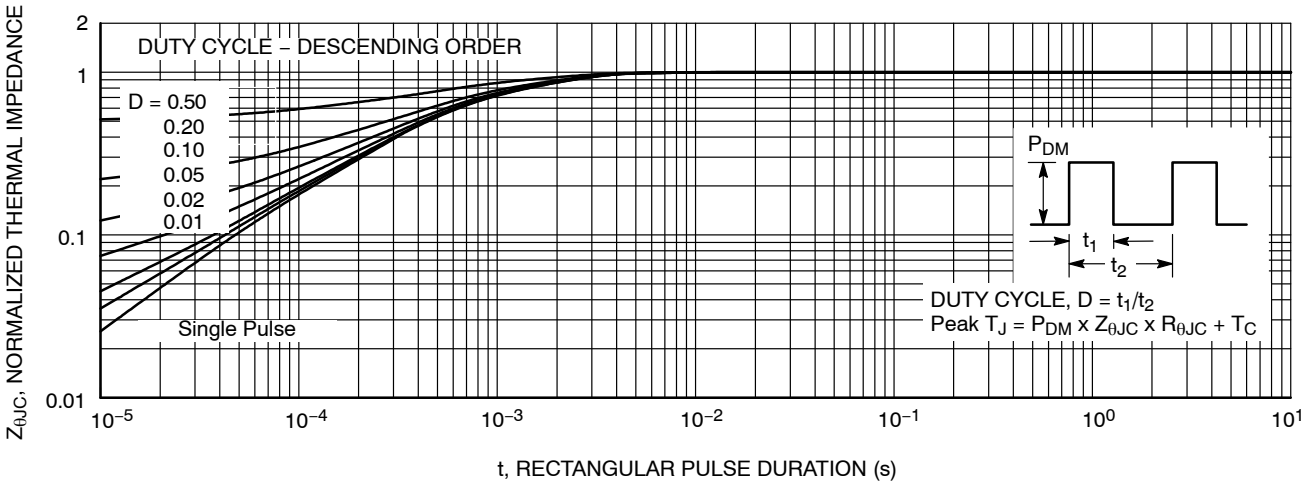


Figure 3. Normalized Maximum Transient Thermal Impedance

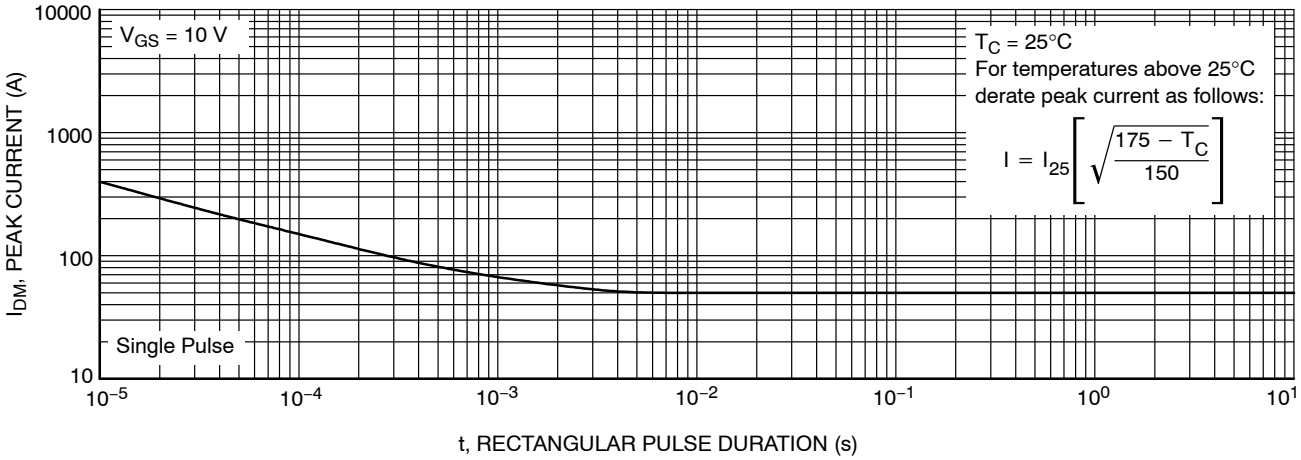


Figure 4. Peak Current Capability

TYPICAL CHARACTERISTICS (continued)

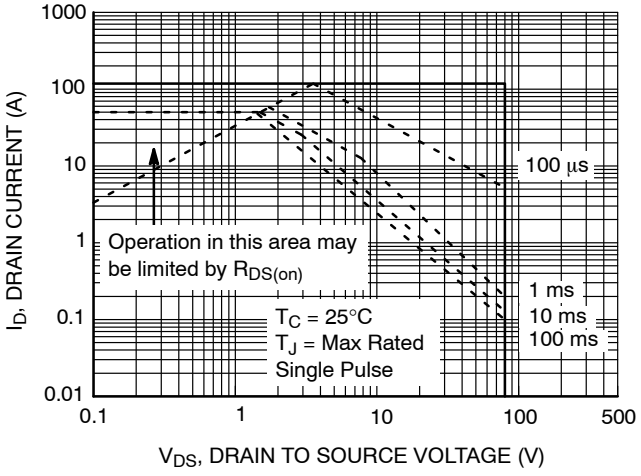
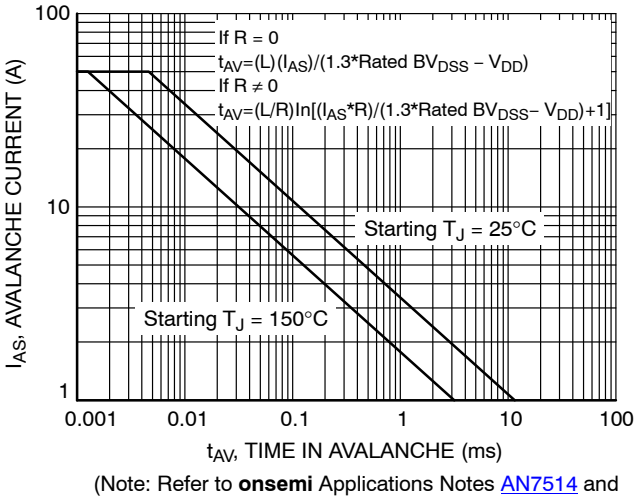


Figure 5. Forward Bias Safe Operating Area



(Note: Refer to **onsemi** Applications Notes AN7514 and AN7515)

Figure 6. Unclamped Inductive Switching Capability

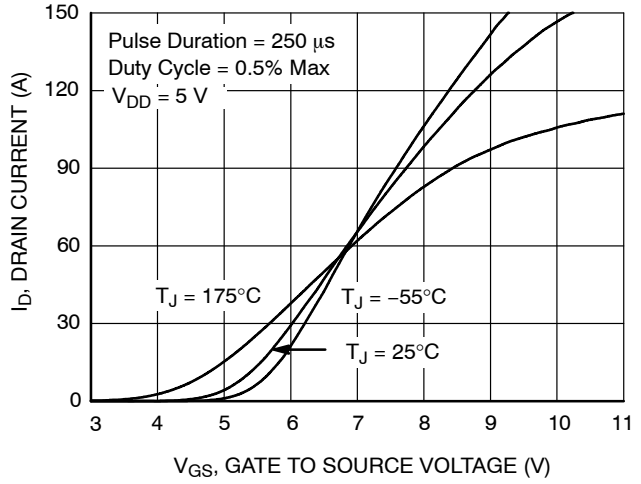


Figure 7. Transfer Characteristics

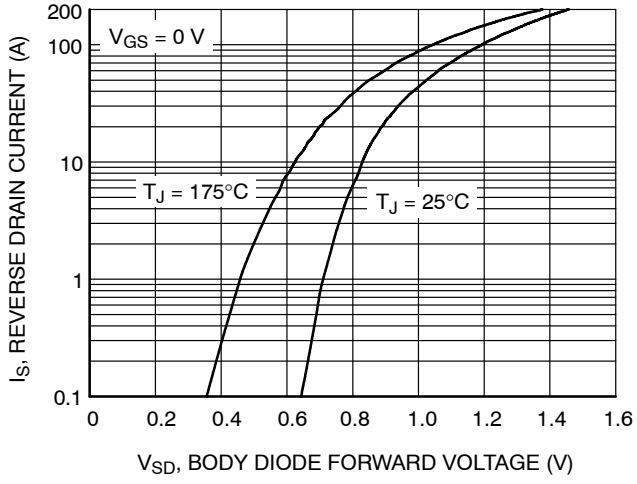


Figure 8. Forward Diode Characteristics

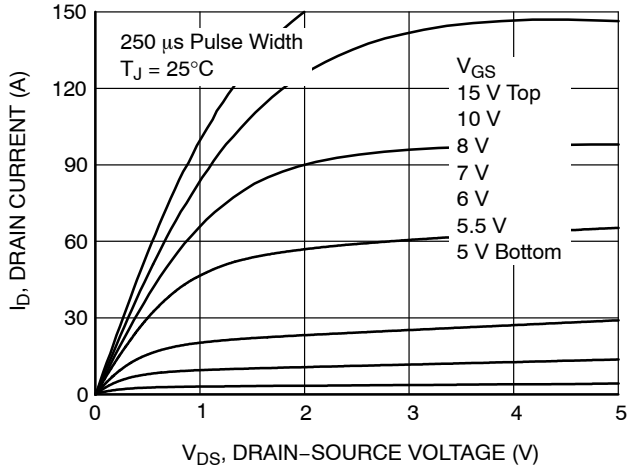


Figure 9. Saturation Characteristics

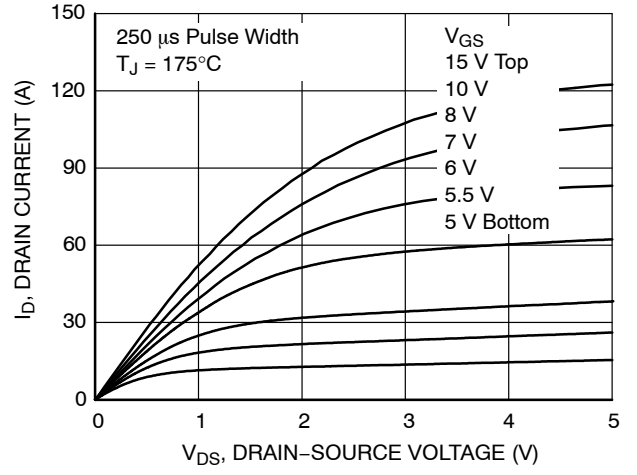


Figure 10. Saturation Characteristics

TYPICAL CHARACTERISTICS (continued)

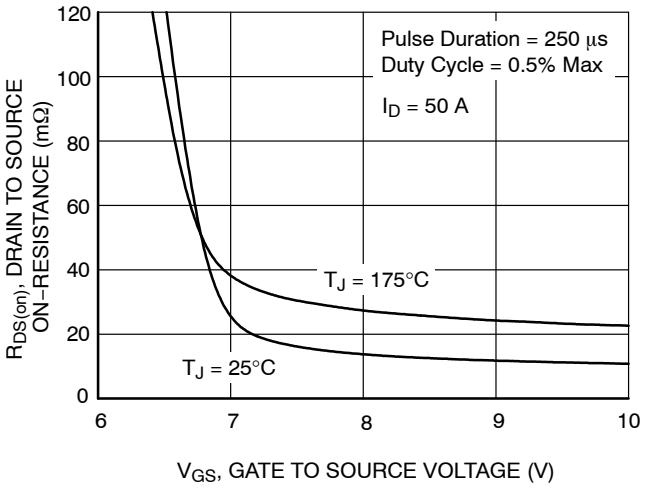


Figure 11. $R_{DS(on)}$ vs. Gate Voltage

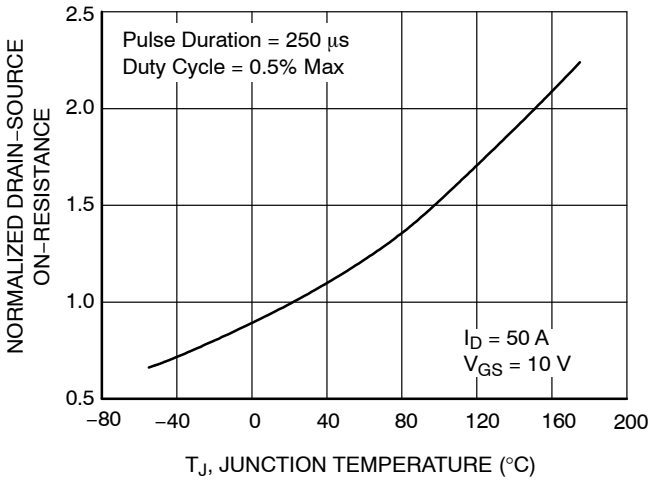


Figure 12. Normalized $R_{DS(on)}$ vs. Junction Temperature

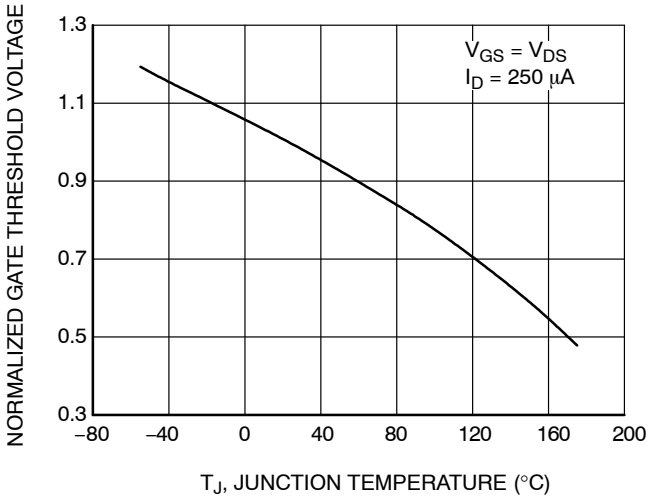


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

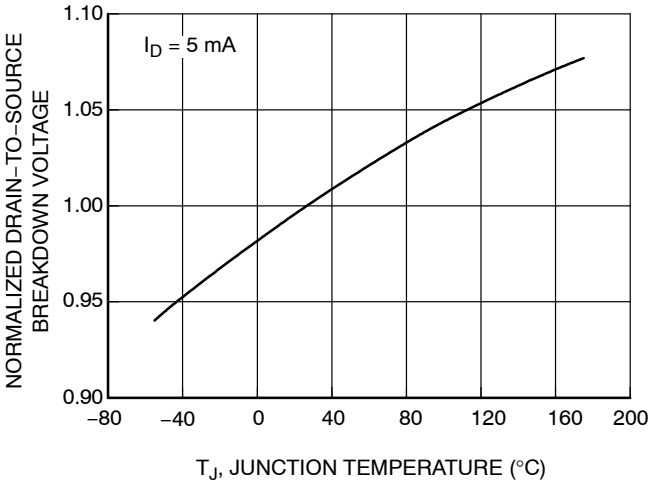


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

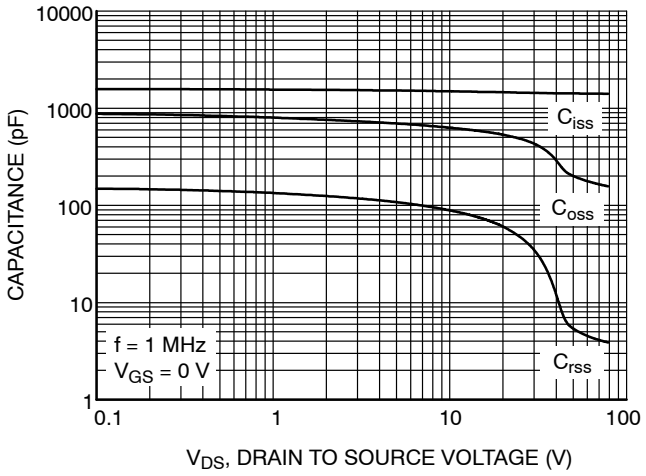


Figure 15. Capacitance vs. Drain to Source Voltage

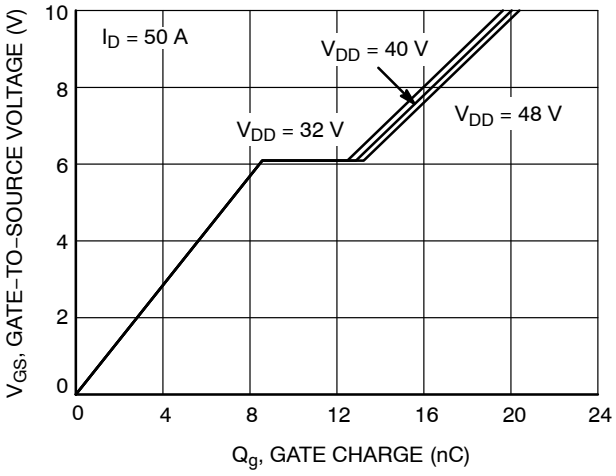
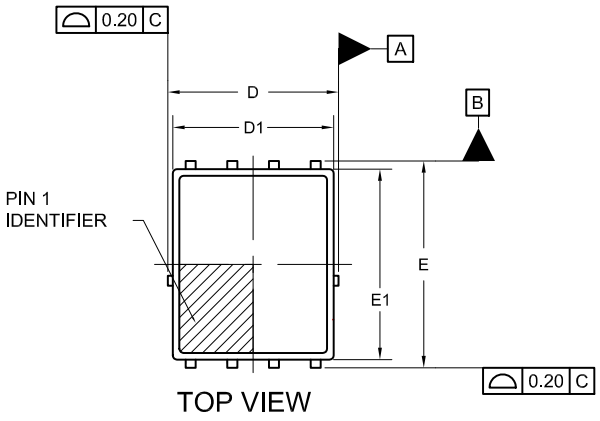


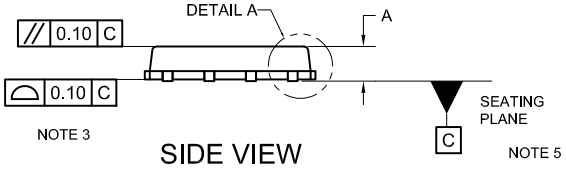
Figure 16. Gate Charge vs. Gate to Source Voltage

PQFN8 5X6, 1.27P
CASE 483BJ
ISSUE C

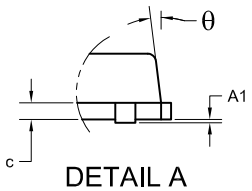
DATE 13 DEC 2017



TOP VIEW



SIDE VIEW

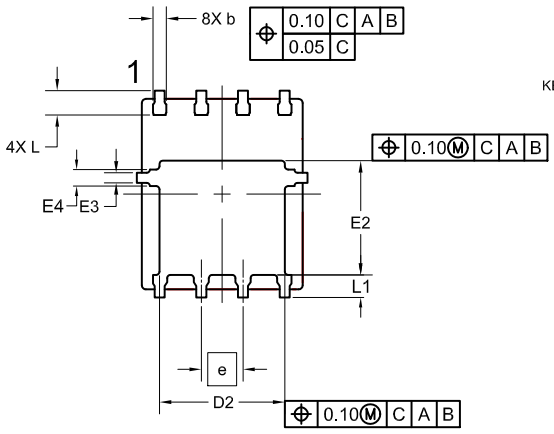


DETAIL A

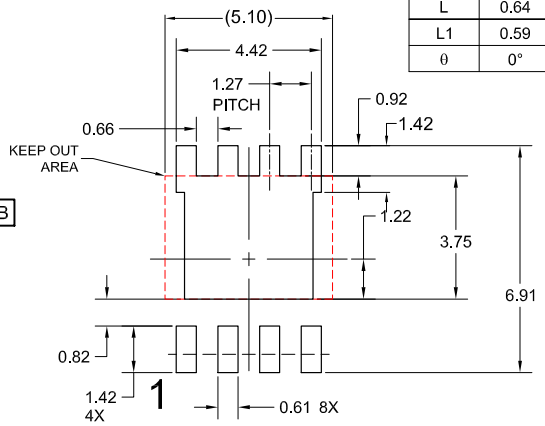
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. A1 IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	0.025	0.05
b	0.31	0.41	0.51
c	0.23	0.28	0.33
D	4.90	5.00	5.10
D1	4.80	4.90	5.00
D2	3.72	3.82	3.92
E	6.20	6.30	6.40
E1	5.70	5.80	5.90
E2	3.38	3.48	3.58
E3	0.30		
E4	0.50		
e	1.27 BSC		
L	0.64	0.74	0.84
L1	0.59	0.69	0.79
θ	0°	—	12°



BOTTOM VIEW



RECOMMENDED
MOUNTING FOOTPRINT

DOCUMENT NUMBER:	**98AON13688G**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**PQFN8 5X6, 1.27P**	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales